

4M x 72 DRAM MODULE

Features

- 168 Pin JEDEC Standard, 8 Byte Dual In-line Memory Module
- 4Mx72 Fast Page Mode DIMM
- Performance:

		-60	-70
t_{RAC}	RAS Access Time	60ns	70ns
t_{CAC}	CAS Access Time	20ns	25ns
t_{AA}	Access Time From Address	36ns	41ns
t_{RC}	Cycle Time	110ns	130ns
t_{PC}	Fast Page Mode Cycle Time	40ns	45ns

- All inputs and outputs are fully TTL compatible
- Single 5V \pm 0.5V Power Supply
- Au contacts

- Optimized for byte-write parity applications
- System Performance Benefits:
 - Buffered inputs (except \overline{RAS} , Data)
 - Reduced noise (32 V_{SS}/V_{CC} pins)
 - 4 Byte Interleave enabled
 - Byte write, byte read accesses
 - Buffered PDs
- Fast Page Mode
- Refresh Modes: \overline{RAS} -Only, CBR and Hidden Refresh
- 4096 refresh cycles distributed across 64ms
- 12/11 (redundant) addressing (Row/Column)
- Card size: 5.25" x 1.0" x 0.354"
- DRAMS in SOJ Package

Description

IBM11M4720D is an industry standard 168-pin 8-byte Dual In-line Memory Module (DIMM) which is organized as a 4Mx72 high speed memory array for parity applications. The DIMM uses 16 4Mx4 (12/10 addressed) DRAMs and 8 4Mx1 (11/11 addressed) DRAMs in SOJ packages.

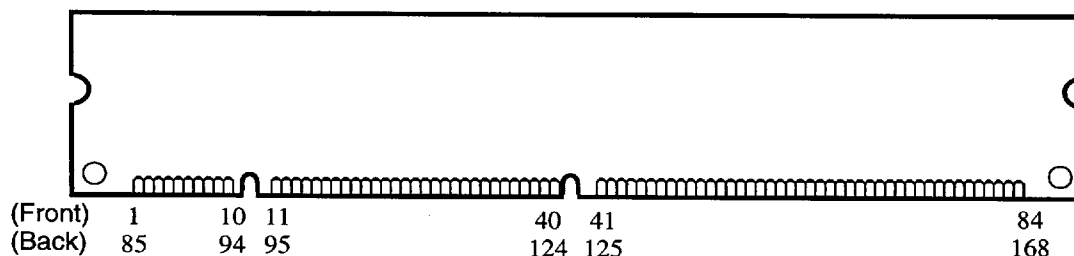
Improved system performance is provided by the on-DIMM buffering of selected input signals. The specified timings include all buffer, net and skew delays, which simplifies the memory subsystem design analysis. The data and RAS signals are not buffered, which preserves the DRAM access specifications of 60ns and 70ns.

Presence Detect (PD) and Identification Detect (ID) bits provide information about the DIMM density,

addressing, performance and features. PD bits can be dotted at the system level and activated for each DIMM position using the PD enable (\overline{PDE}) signal. ID bits also allow detection of card features, and may be dot-or'd at the system level to provide information for the entire DIMM bank. For example, if a x64 or x72 (ECC) DIMM were inserted into a bank of x72 parity DIMMs, ID0 (grounded) would indicate that at least one DIMM in that memory bank will not function properly. PD8 would indicate what positions, if any, contained an ECC DIMM.

All IBM 168-pin DIMMs provide a high performance, flexible 8-byte interface in a 5.25" long space-saving footprint. Related products are the x64 non-parity (5V) and ECC DIMMs (5V and 3.3V).

Card Outline





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Pin Description

RAS0, RAS2	Row Address Strobe
CAS0 - CAS7	Column Address Strobe (Buffered)
WE0, WE2	Read/write Input (Buffered)
OE0, OE2	Output Enable (Buffered)
A0, B0, A1 - A11	Address Inputs (Buffered)
DQx	Data Input/output
PQx	Parity Input/output
Vcc	Power (+5V)
Vss	Ground
NC	No Connect
PD1 - PD8	Presence Detects (Buffered)
PDE	Presence Detect Enable
ID0 - ID1	ID Bits

Pinout

Pin#	Front Side	Pin#	Back Side	Pin#	Front Side	Pin#	Back Side
1	Vss	85	Vss	43	Vss	127	Vss
2	DQ0	86	DQ36	44	OE2	128	NC
3	DQ1	87	DQ37	45	RAS2	129	NC
4	DQ2	88	DQ38	46	CAS4	130	CAS5
5	DQ3	89	DQ39	47	CAS6	131	CAS7
6	Vcc	90	Vcc	48	WE2	132	PDE
7	DQ4	91	DQ40	49	Vcc	133	Vcc
8	DQ5	92	DQ41	50	NC	134	NC
9	DQ6	93	DQ42	51	NC	135	NC
10	DQ7	94	DQ43	52	DQ18	136	DQ54
11	PQ8	95	PQ44	53	DQ19	137	DQ55
12	Vss	96	Vss	54	Vss	138	Vss
13	DQ9	97	DQ45	55	DQ20	139	DQ56
14	DQ10	98	DQ46	56	DQ21	140	DQ57
15	DQ11	99	DQ47	57	DQ22	141	DQ58
16	DQ12	100	DQ48	58	DQ23	142	DQ59
17	DQ13	101	DQ49	59	Vcc	143	Vcc
18	Vcc	102	Vcc	60	DQ24	144	DQ60
19	DQ14	103	DQ50	61	NC	145	NC
20	DQ15	104	DQ51	62	NC	146	NC
21	DQ16	105	DQ52	63	NC	147	NC
22	PQ17	106	PQ53	64	NC	148	NC
23	Vss	107	Vss	65	DQ25	149	DQ61
24	NC	108	NC	66	PQ26	150	PQ62
25	NC	109	NC	67	DQ27	151	DQ63
26	Vcc	110	Vcc	68	Vss	152	Vss
27	WE0	111	NC	69	DQ28	153	DQ64
28	CAS0	112	CAS1	70	DQ29	154	DQ65
29	CAS2	113	CAS3	71	DQ30	155	DQ66
30	RAS0	114	NC	72	DQ31	156	DQ67
31	OE0	115	NC	73	Vcc	157	Vcc
32	Vss	116	Vss	74	DQ32	158	DQ68
33	A0	117	A1	75	DQ33	159	DQ69
34	A2	118	A3	76	DQ34	160	DQ70
35	A4	119	A5	77	PQ35	161	PQ71
36	A6	120	A7	78	Vss	162	Vss
37	A8	121	A9	79	PD1	163	PD2
38	A10	122	A11	80	PD3	164	PD4
39	NC	123	NC	81	PD5	165	PD6
40	Vcc	124	Vcc	82	PD7	166	PD8
41	NC	125	NC	83	ID0	167	ID1
42	NC	126	B0	84	Vcc	168	Vcc

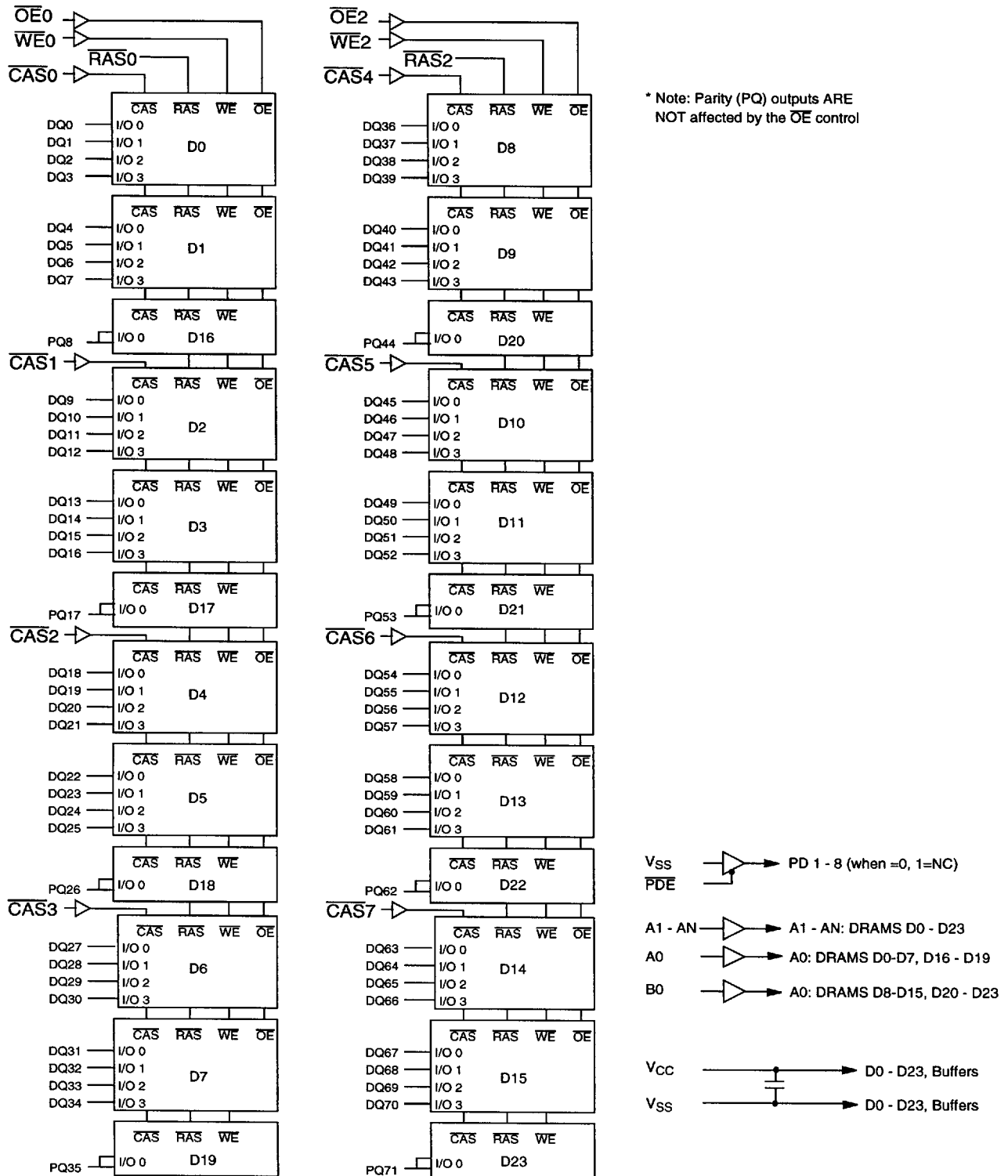
Note: All pin assignments are consistent for all 8 Byte versions.

Ordering Information

Part Number	Organization	Speed	Addr.	Leads	Dimension	Power	Notes
IBM11M4720D-60	4Mx72	60ns	12/11	Au	5.25"x1.0"x0.354"	5.0V	1
IBM11M4720D-70		70ns					
IBM11M4720D-60J		60ns					
IBM11M4720D-70J		70ns					
1. DRAM package designator appended to speed portion of part number on assemblies beginning with DRAM die rev E.							



Block Diagram



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4M x 72 DRAM MODULE

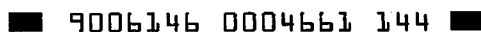
Truth Table

Function	RAS	CAS	WE	OE	Row Address	Column Address	PDE	DQx	
Standby	H	H→X	X	X	X	X	X	High Impedance	
Read	L	L	H	L	Row	Col	X	Valid Data Out	
Early-Write	L	L	L	X	Row	Col	X	Valid Data In	
Fast Page Mode - Read 1st Cycle	L	H→L	H	L	Row	Col	X	Valid Data Out	
Subsequent Cycles	L	H→L	H	L	N/A	Col	X	Valid Data Out	
Fast Page Mode - Write 1st Cycle	L	H→L	L	X	Row	Col	X	Valid Data In	
Subsequent Cycles	L	H→L	L	X	N/A	Col	X	Valid Data In	
RAS-Only Refresh	L	H	X	X	Row	N/A	X	High Impedance	
CAS-Before-RAS Refresh	H→L	L	H	X	X	X	X	High Impedance	
Hidden Refresh	Read	L→H→L	L	H	L	Row	Col	X	Data Out
	Write	L→H→L	L	H	X	Row	Col	X	Data In
Read Presence Detects	X	X	X	X	X	X	L	Not Affected (PD Bits Valid)	

Presence Detect

Pin	-60	-70
PD1 (PD1 - PD4: Addressing/Density)	1	1
PD2	1	1
PD3	0	0
PD4	1	1
PD5 (EDO Detection)	0	0
PD6 (PD6 - PD7: Speed)	1	0
PD7	1	1
PD8 (Parity/ECC Designator)	1	1
ID0 (DIMM Type/Width)	1	1
ID1 (Refresh Mode)	0	0

1. PD1-8 are buffered outputs (0 = driven to V_{OL}, 1 = open)
 2. ID0-1 are unbuffered outputs (0 = V_{SS}, 1 = open)
 3. PDE should be tied high or low at system level if not used



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	Notes
V_{CC}	Power Supply Voltage	-1.0 to +7.0	V	1
V_{IN}	Input Voltage	-0.5 to min ($V_{CC} + 0.5$, 7.0)	V	1
V_{OUT}	Output Voltage	-0.5 to min ($V_{CC} + 0.5$, 7.0)	V	1
T_{OPR}	Operating Temperature	0 to +70	°C	1
T_{STG}	Storage Temperature	-55 to +125	°C	1
P_D	Power Dissipation	12.3	W	1
I_{OUT}	Short Circuit Output Current	50	mA	1
I_{OUTPD}	Short Circuit Output Current (PD)	60	mA	1

1. Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated is not implied. Exposure to absolute maximum rating condition for extended periods may affect reliability.

Recommended DC Operating Conditions ($T_A = 0$ to 70°C)

Symbol	Parameter	Min	Typ	Max	Units	Notes
V_{CC}	Supply Voltage	4.5	5.0	5.5	V	1
V_{IH}	Input High Voltage	2.4	—	V_{CC}	V	1, 2
V_{IL}	Input Low Voltage	-0.5	—	0.8	V	1, 2

1. All voltages referenced to V_{SS} .
 2. V_{IH} may overshoot to $V_{CC} + 2.0\text{V}$ for pulse widths of $\leq 4.0\text{ns}$ (or $V_{CC} + 1.0\text{V}$ for $\leq 8.0\text{ns}$). Additionally, V_{IL} may undershoot to -2.0V for pulse widths $\leq 4.0\text{ns}$ (or -1.0V for $\leq 8.0\text{ns}$). Pulse widths measured at 50% points with amplitude measured peak to DC reference.

Capacitance ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5.0\text{V} \pm 0.5\text{V}$)

Symbol	Parameter	Max	Units
C_{I1}	Input Capacitance (A0, B0, A1-A11)	13	pF
C_{I2}	Input Capacitance ($\overline{\text{RAS}}$)	90	pF
C_{I3}	Input Capacitance ($\overline{\text{CAS}}$, WE, OE)	13	pF
C_{I4}	Input Capacitance ($\overline{\text{PDE}}$)	18	pF
C_{IO1}	Input/Output Capacitance (DQx)	15	pF
C_{IO2}	Input/Output Capacitance (PQx)	20	pF
C_{O1}	Output Capacitance (PD)	15	pF
C_{O2}	Output Capacitance (ID)	5	pF

4M x 72 DRAM MODULE

DC Electrical Characteristics ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5.0\text{V} \pm 0.5\text{V}$)

Symbol	Parameter	Min	Max	Units	Notes	
I_{CC1}	Operating Current Average Power Supply Operating Current ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$, Address Cycling: $t_{RC} = t_{RC \text{ min}}$)	-60	—	2240	mA	1,2,3
		-70	—	2000		
I_{CC2}	Standby Current (TTL) Power Supply Standby Current ($\overline{\text{RAS}} = \overline{\text{CAS}} \geq V_{IH}$)	—	48	mA		
I_{CC3}	$\overline{\text{RAS}}$ Only Refresh Current Average Power Supply Current, $\overline{\text{RAS}}$ Only Mode ($\overline{\text{RAS}}$ Cycling, $\overline{\text{CAS}} \geq V_{IH}$; $t_{RC} = t_{RC \text{ min}}$)	-60	—	2240	mA	1,3
		-70	—	2000		
I_{CC4}	Fast Page Mode Current Average Power Supply Current, Fast Page Mode ($\overline{\text{RAS}} \leq V_{IL}$, $\overline{\text{CAS}}$, Address Cycling: $t_{PC} = t_{PC \text{ min}}$)	-60	—	1840	mA	1,2,3
		-70	—	1600		
I_{CC5}	Standby Current (CMOS) Power Supply Standby Current ($\overline{\text{RAS}} = \overline{\text{CAS}} = V_{CC} - 0.2\text{V}$)	—	24	mA		
I_{CC6}	$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Refresh Current Average Power Supply Current, $\overline{\text{CAS}}$ Before $\overline{\text{RAS}}$ Mode ($\overline{\text{RAS}}$, $\overline{\text{CAS}}$, Cycling: $t_{RC} = t_{RC \text{ min}}$)	-60	—	2240	mA	1,3
		-70	—	2000		
I_{IL}	Input Leakage Current Input Leakage Current, any Input ($0.0 \leq V_{IN} \leq (V_{CC} - 6.0\text{V})$), All Other Pins Not Under Test = 0V	All but $\overline{\text{RAS}}$	-10	+10	μA	
		$\overline{\text{RAS}}$	-120	+120		
I_{OL}	Output Leakage Current (D_{OUT} is disabled, $0.0 \leq V_{OUT} \leq V_{CC}$)	-10	+10	μA		
V_{OH}	Output High Level Output "H" Level Voltage ($I_{OUT} = -5\text{mA} @ 2.4\text{V}$)	2.4	—	V		
V_{OL}	Output Low level Output "L" Level Voltage ($I_{OUT} = +4.2\text{mA} @ 0.4\text{V}$)	—	0.4	V		

1. I_{CC1} , I_{CC3} , I_{CC4} and I_{CC6} depend on cycle rate.
2. I_{CC1} , I_{CC4} depend on output loading. Specified values are obtained with output open.
3. Address can be changed once or less while $\overline{\text{RAS}} = V_{IL}$. In the case of I_{CC4} , it can be changed once or less when $\overline{\text{CAS}} = V_{IH}$.

**AC Characteristics** ($T_A = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5.0\text{V} \pm 0.5\text{V}$)

- V_{IH} (min) and V_{IL} (max) are reference levels for measuring timing of input signals. Transition times are measured between V_{IH} and V_{IL} .
- An initial pause of $200\mu\text{s}$ is required after power-up followed by 8 $\overline{\text{RAS}}$ only refresh cycles before proper device operation is achieved. In case of using internal refresh counter, a minimum of 8 $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles instead of 8 $\overline{\text{RAS}}$ only refresh cycles is required.
- The specified timings include buffer, loading and skew delay adders: 2ns minimum, 5ns ($\overline{\text{CAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$), or 6ns (address) maximum delay, no pulse shrinkage to the DRAM device timings. The data and $\overline{\text{RAS}}$ signals are not buffered, which preserves the DRAM access specifications of 60ns and 70ns.
- AC measurements assume $t_T = 5\text{ns}$.

Read, Write and Refresh Cycles (Common Parameters)

Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{RC}	Random Read or Write Cycle Time	110	—	130	—	ns	
t_{RP}	$\overline{\text{RAS}}$ Precharge Time	40	—	50	—	ns	
t_{CP}	$\overline{\text{CAS}}$ Precharge Time	10	—	10	—	ns	
t_{RAS}	$\overline{\text{RAS}}$ Pulse Width	60	10K	70	10K	ns	
t_{CAS}	$\overline{\text{CAS}}$ Pulse Width	15	10K	20	10K	ns	1
t_{ASR}	Row Address Setup Time	6	—	6	—	ns	
t_{RAH}	Row Address Hold Time	8	—	8	—	ns	
t_{ASC}	Column Address Setup Time	4	—	4	—	ns	
t_{CAH}	Column Address Hold Time	10	—	10	—	ns	
t_{RCD}	$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Delay Time	18	40	18	45	ns	2
t_{RAD}	$\overline{\text{RAS}}$ to Column Address Delay Time	13	24	13	29	ns	3
t_{RSH}	$\overline{\text{RAS}}$ Hold Time	20	—	25	—	ns	
t_{CSH}	$\overline{\text{CAS}}$ Hold Time	58	—	68	—	ns	
t_{CRP}	$\overline{\text{CAS}}$ to $\overline{\text{RAS}}$ Precharge Time	10	—	10	—	ns	
t_{ODD}	$\overline{\text{OE}}$ to D_{IN} Delay Time	20	—	25	—	ns	4, 6
t_{DZO}	$\overline{\text{OE}}$ Delay Time from D_{IN}	-2	—	-2	—	ns	5, 6
t_{DZC}	$\overline{\text{CAS}}$ Delay Time from D_{IN}	-2	—	-2	—	ns	5
t_{AR}	Column Address Hold Time Referenced to $\overline{\text{RAS}}$	57	—	62	—	—	
t_T	Transition Time (Rise and Fall)	3	30	3	30	ns	

- The minimum t_{CAS} requires t_{CSH} to be met for both writes and reads. Also, because of the buffer, the minimum t_{CAS} for a read cycle must be extended to guarantee the data out window (t_{OH}) in the application. For example, a t_{CAS} of 15ns plus a minimum t_{OH} of 2ns would result in turning data out of the DIMM at 17ns (3ns before max t_{CAC} of 20ns).
- Operation within the $t_{RCD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met. The $t_{RCD}(\text{max})$ is specified as a reference point only: If t_{RCD} is greater than the specified $t_{RCD}(\text{max})$ limit, then access time is controlled by t_{CAC} .
- Operation within the $t_{RAD}(\text{max})$ limit ensures that $t_{RAC}(\text{max})$ can be met. The $t_{RAD}(\text{max})$ is specified as a reference point only: If t_{RAD} is greater than the specified $t_{RAD}(\text{max})$ limit, then access time is controlled by t_{AA} .
- Either t_{CDD} or t_{ODD} must be satisfied.
- Either t_{DZC} or t_{DZO} must be satisfied.
- $\overline{\text{OE}}$ has no effect on Parity (PQx) bits.

4M x 72 DRAM MODULE

Write Cycle

Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{WCS}	Write Command Setup Time	2	—	2	—	ns	1
t_{WCH}	Write Command Hold Time	17	—	17	—	ns	
t_{WP}	Write Command Pulse Width	15	—	15	—	ns	
t_{RWL}	Write Command to \overline{RAS} Lead Time	20	—	25	—	ns	
t_{CWL}	Write Command to \overline{CAS} Lead Time	17	—	22	—	ns	
t_{WCR}	Write Command Hold Time Referenced to \overline{RAS}	47	—	57	—	ns	
t_{DHR}	Data Hold Time Referenced to \overline{RAS}	50	—	55	—	ns	
t_{DS}	D_{IN} Setup Time	-2	—	-2	—	ns	
t_{DH}	D_{IN} Hold Time	17	—	20	—	ns	

1. t_{WCS} , t_{RWD} , t_{CWD} , t_{AWD} , and t_{CPW} are not restrictive parameters. They are included in the data sheet as electrical characteristics only. If $t_{WCS} \geq t_{WCS}(\text{min.})$, the entire cycle is an early write cycle and the data pin will remain open circuit (high impedance) through the entire cycle; If $t_{RWD} \geq t_{RWD}(\text{min.})$, $t_{CWD} \geq t_{CWD}(\text{min.})$, $t_{AWD} \geq t_{AWD}(\text{min.})$ and $t_{CPW} \geq t_{CPW}(\text{min.})$ (Fast Page Mode), the cycle is a Read-Modify-Write cycle and the data will contain read from the selected cell; If neither of the above sets of conditions are met, the condition of the data (at access time) is indeterminate.

**Read Cycle**

Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{RAC}	Access Time from \overline{RAS}	—	60	—	70	ns	1, 2
t_{CAC}	Access Time from \overline{CAS}	—	20	—	25	ns	1, 2
t_{AA}	Access Time from Address	—	36	—	41	ns	1, 2
t_{OEA}	Access Time from \overline{OE}	—	20	—	25	ns	1, 2, 3
t_{RCS}	Read Command Setup Time	2	—	2	—	ns	
t_{RCH}	Read Command Hold Time to \overline{CAS}	2	—	2	—	ns	4
t_{RRH}	Read Command Hold Time to \overline{RAS}	0	—	0	—	ns	4
t_{RAL}	Column Address to \overline{RAS} Lead Time	36	—	41	—	ns	
t_{CAL}	Column Access to \overline{CAS} Lead Time	36	—	41	—	ns	
t_{CLZ}	\overline{CAS} to Output in Low-Z	2	—	2	—	ns	
t_{RCH}	\overline{RAS} Hold to Output Enable	—	—	—	—	ns	5
t_{OH}	Output Data Hold time	2	—	2	—	ns	
t_{OHO}	Output Data Hold from \overline{OE}	2	—	2	—	ns	3
t_{OEZ}	Output Buffer Turn-off Delay from \overline{OE}	2	20	2	20	ns	3, 6
t_{CDD}	\overline{CAS} to D_{IN} Delay Time	20	—	20	—	ns	7
t_{OFF}	Output Buffer Turn-off Delay	2	20	2	20	ns	6

1. Measured with the specified current load and 100pF.
2. Access time is determined by the latter of t_{RAC} , t_{CAC} , t_{CPA} , t_{AA} , t_{OEA} .
3. \overline{OE} has no effect on Parity (PQx) bits.
4. Either t_{RCH} or t_{RRH} must be satisfied.
5. This timing parameter is not applicable to this product, but applies to a related product in this family.
6. t_{OFF} (max) and t_{OEZ} (max) define the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.
7. Either t_{CDD} or t_{ODD} must be satisfied.

4M x 72 DRAM MODULE

Fast Page Mode Cycle

Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{PC}	Fast Page Mode Cycle Time	40	—	45	—	ns	
t_{RASP}	Fast Page Mode \overline{RAS} Pulse Width	60	100K	70	100K	ns	
t_{CPRH}	\overline{RAS} Hold Time from \overline{CAS} Precharge	40	—	45	—	ns	
t_{CPA}	Access Time from \overline{CAS} Precharge	—	40	—	45	ns	1,2

1. Measured with the specified current load and 100pF.
2. Access time is determined by the latter of t_{RAC} , t_{CAC} , t_{CPA} , t_{AA} , t_{OEA} .

Refresh Cycle

Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{CHR}	\overline{CAS} Hold Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	8	—	8	—	ns	
t_{CSR}	\overline{CAS} Setup Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	14	—	14	—	ns	
t_{WRP}	\overline{WE} Setup Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	15	—	15	—	ns	
t_{WRH}	\overline{WE} Hold Time (\overline{CAS} before \overline{RAS} Refresh Cycle)	8	—	8	—	ns	
t_{RPC}	\overline{RAS} Precharge to \overline{CAS} Hold Time	3	—	3	—	ns	
t_{REF}	Refresh Period	—	64	—	64	ms	1

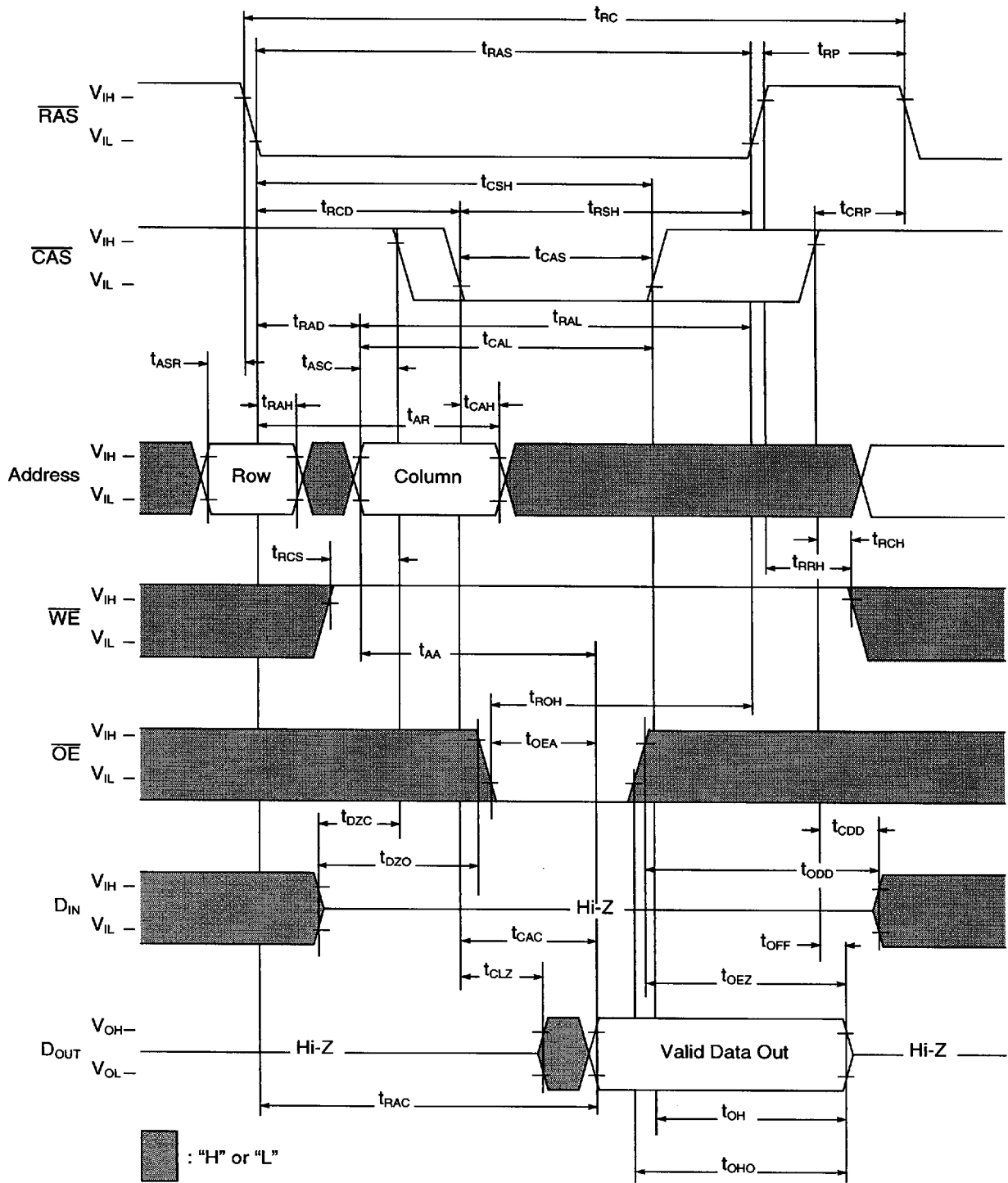
1. 4096 refreshes are required every 64ms (A10 and A11 must be the most significant addresses).

Presence Detect Read Cycle

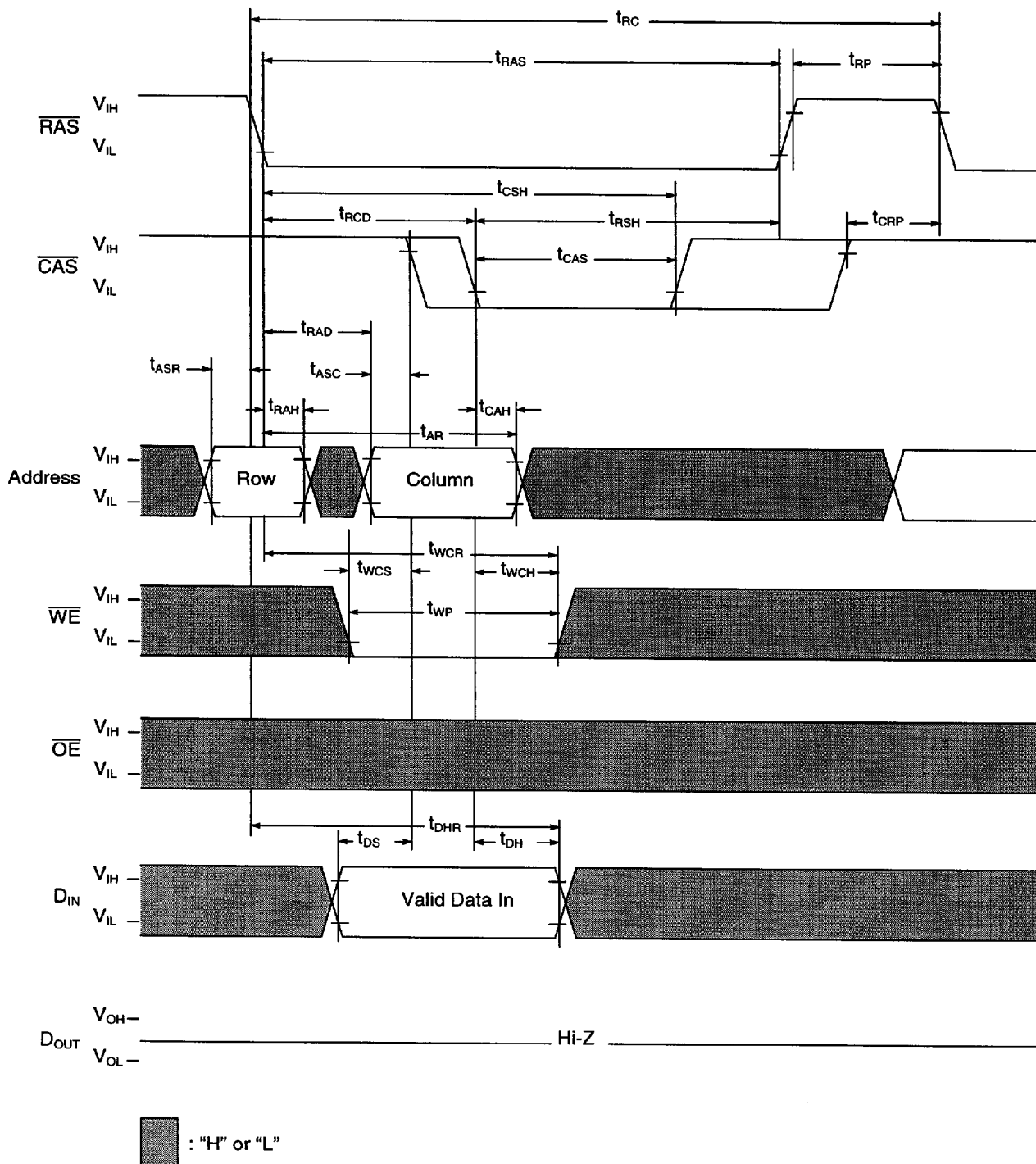
Symbol	Parameter	-60		-70		Unit	Notes
		Min	Max	Min	Max		
t_{PD}	\overline{PDE} to Valid Presence Detect Data	—	10	—	10	ns	1
$t_{PD\text{OFF}}$	\overline{PDE} Inactive to Presence Detects Inactive	0	10	0	10	ns	2

1. Measured with the specified current load and 100pF.
2. $t_{PD\text{OFF}}(\text{max})$ defines the time at which the output achieves the open circuit condition and is not referenced to output voltage levels.

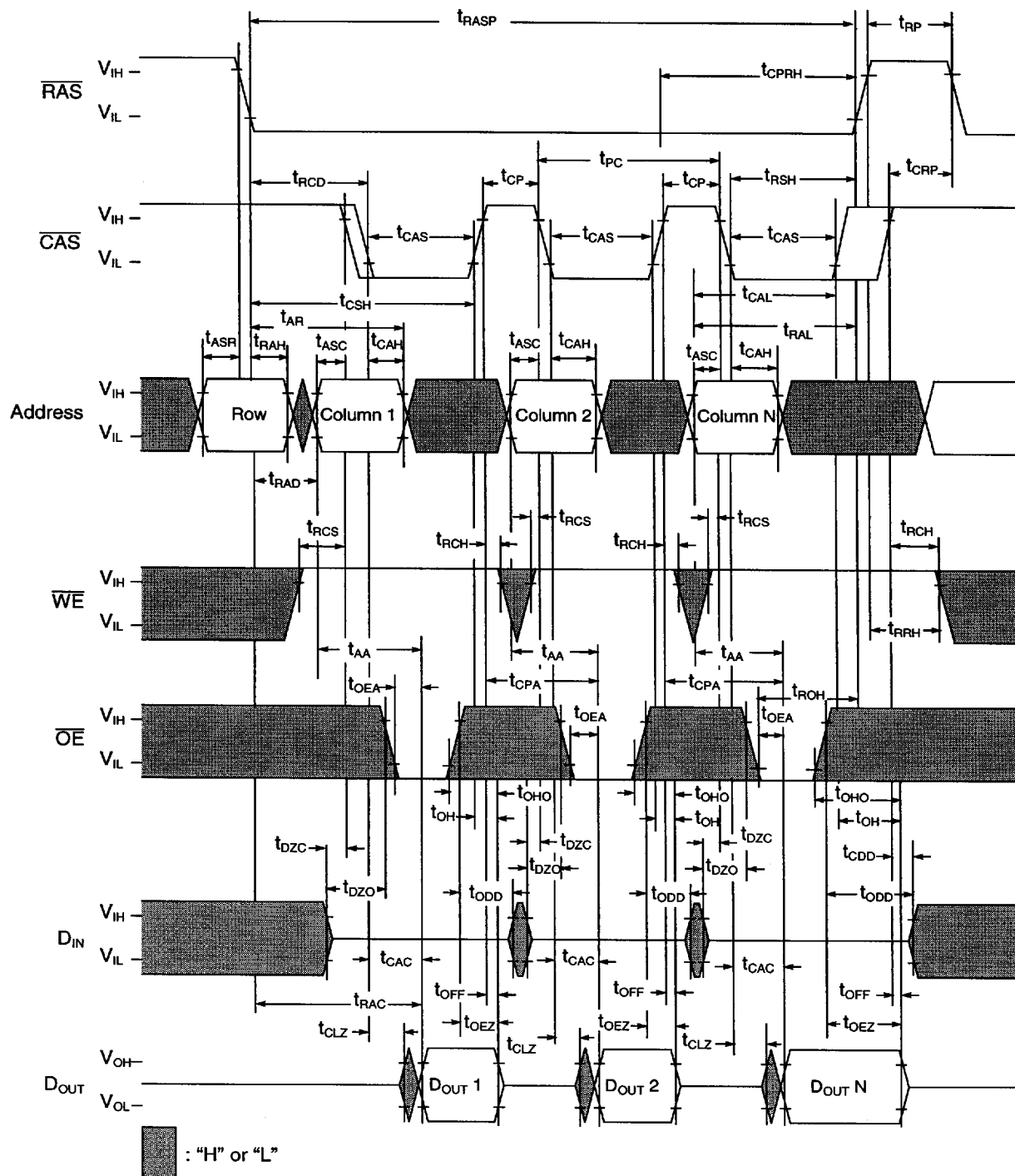
Read Cycle



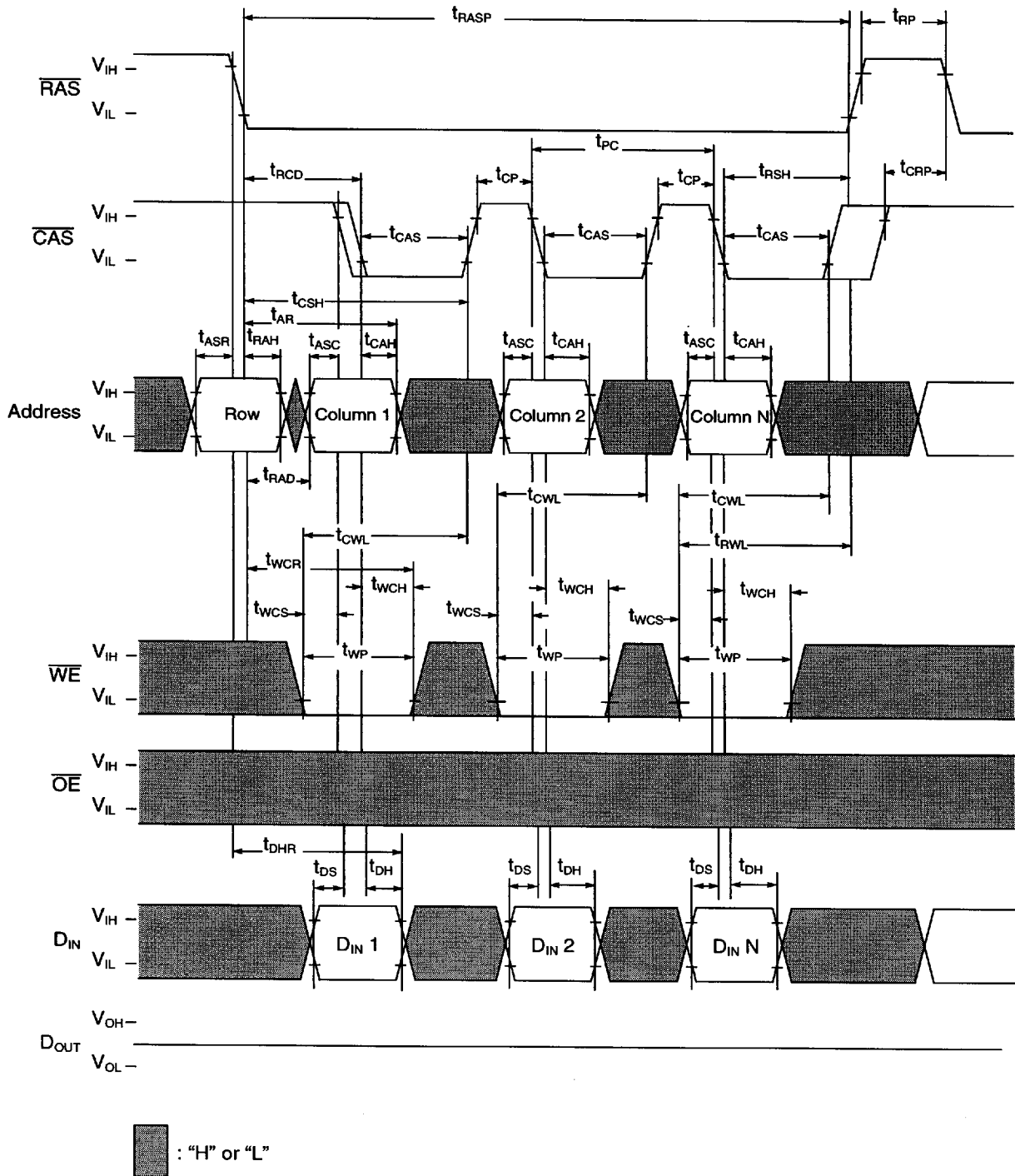
Write Cycle (Early Write)



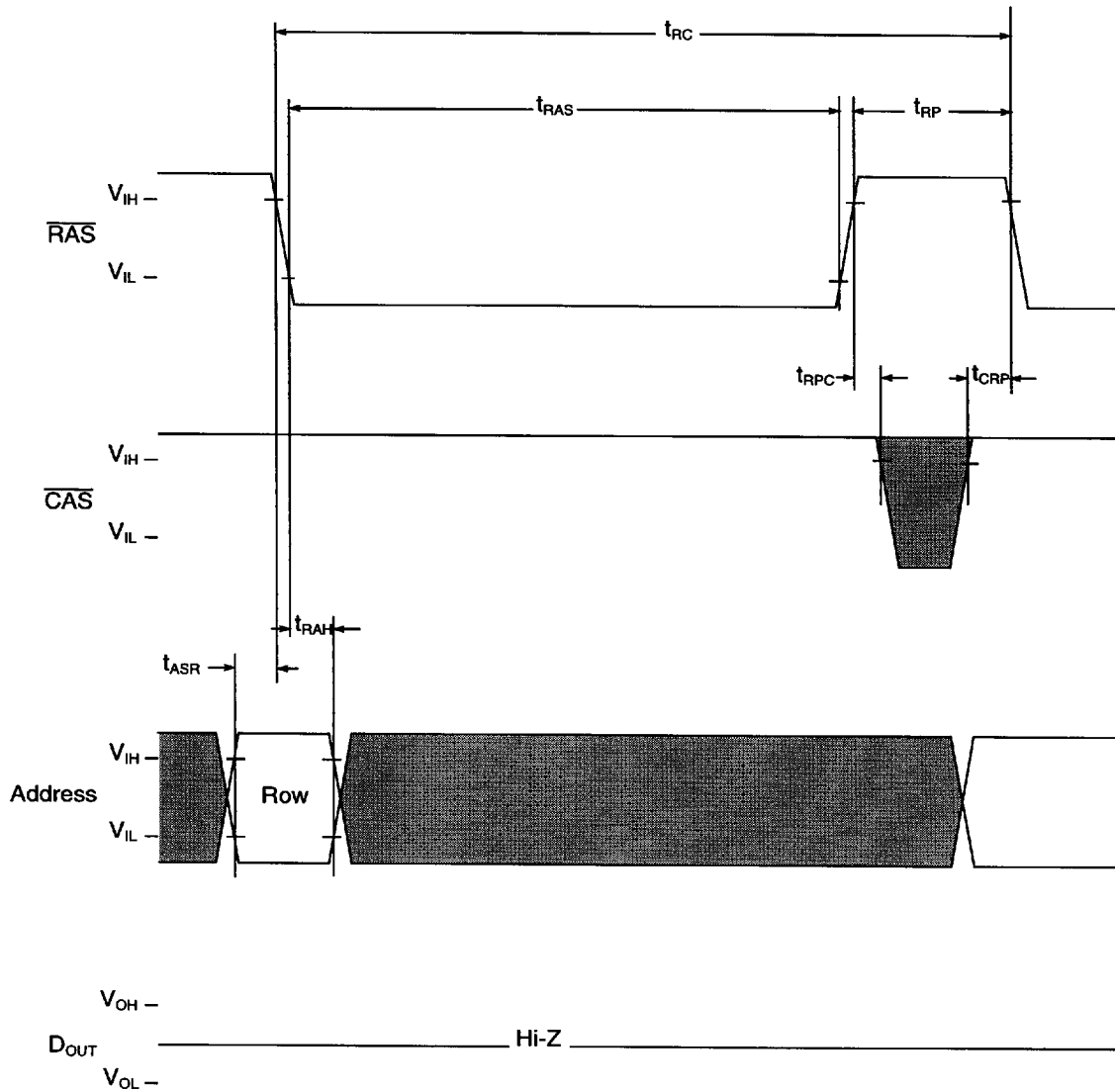
Fast Page Mode Read Cycle




Fast Page Mode Write Cycle



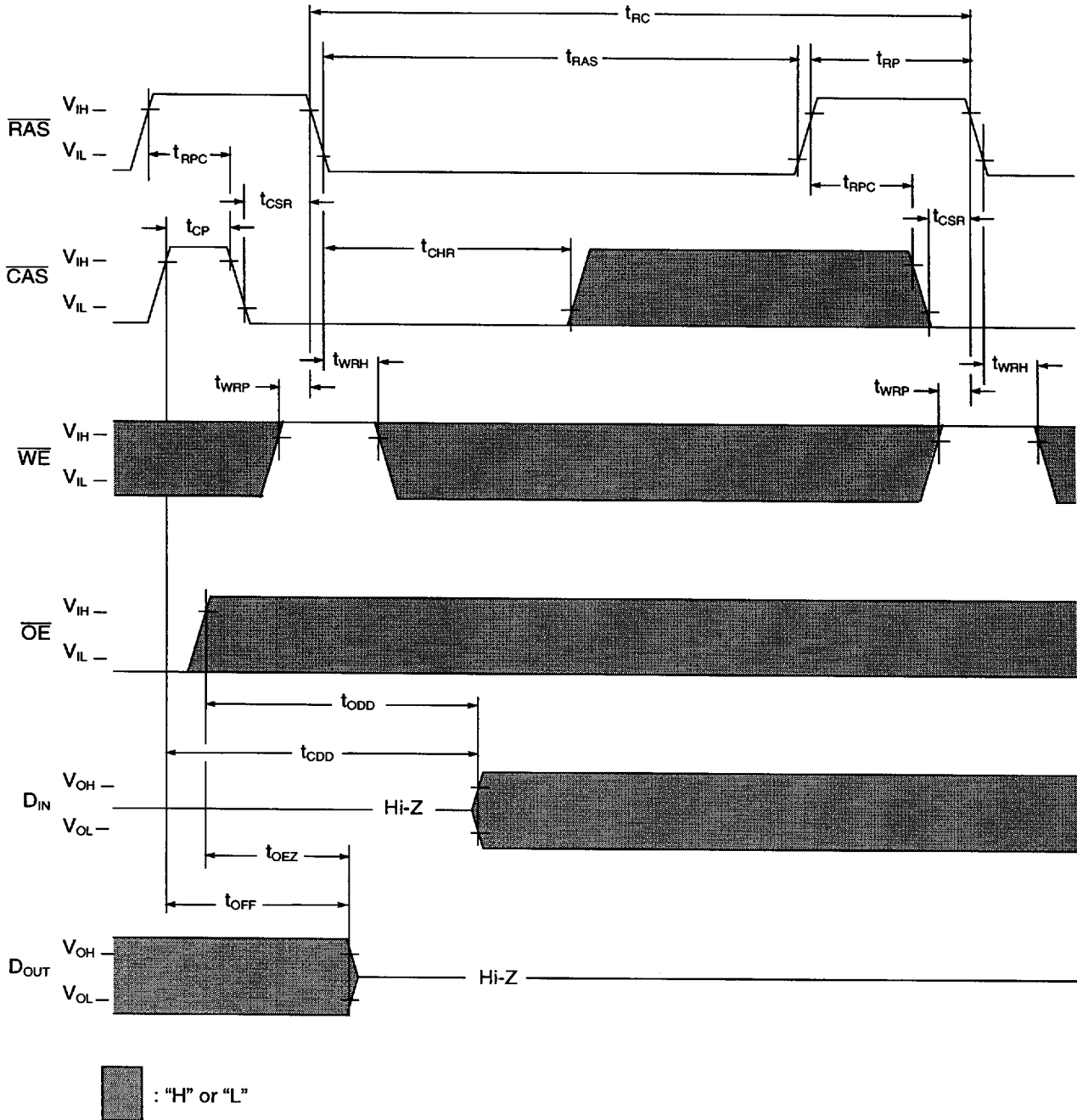
RAS Only Refresh Cycle



 : "H" or "L"

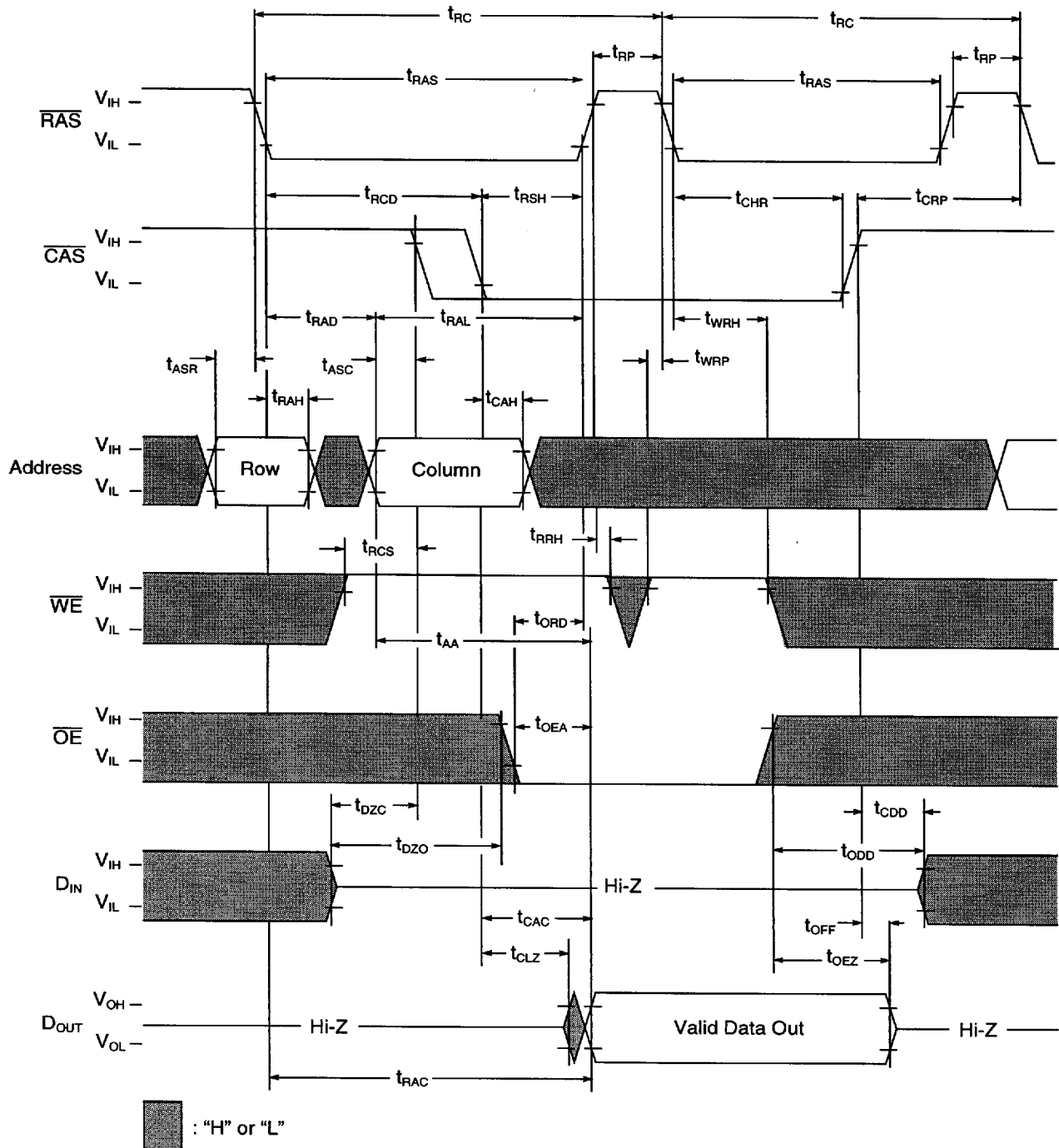
Note: $\overline{\text{WE}}$, $\overline{\text{OE}}$, D_{IN} are "H" or "L"

CAS Before RAS Refresh Cycle

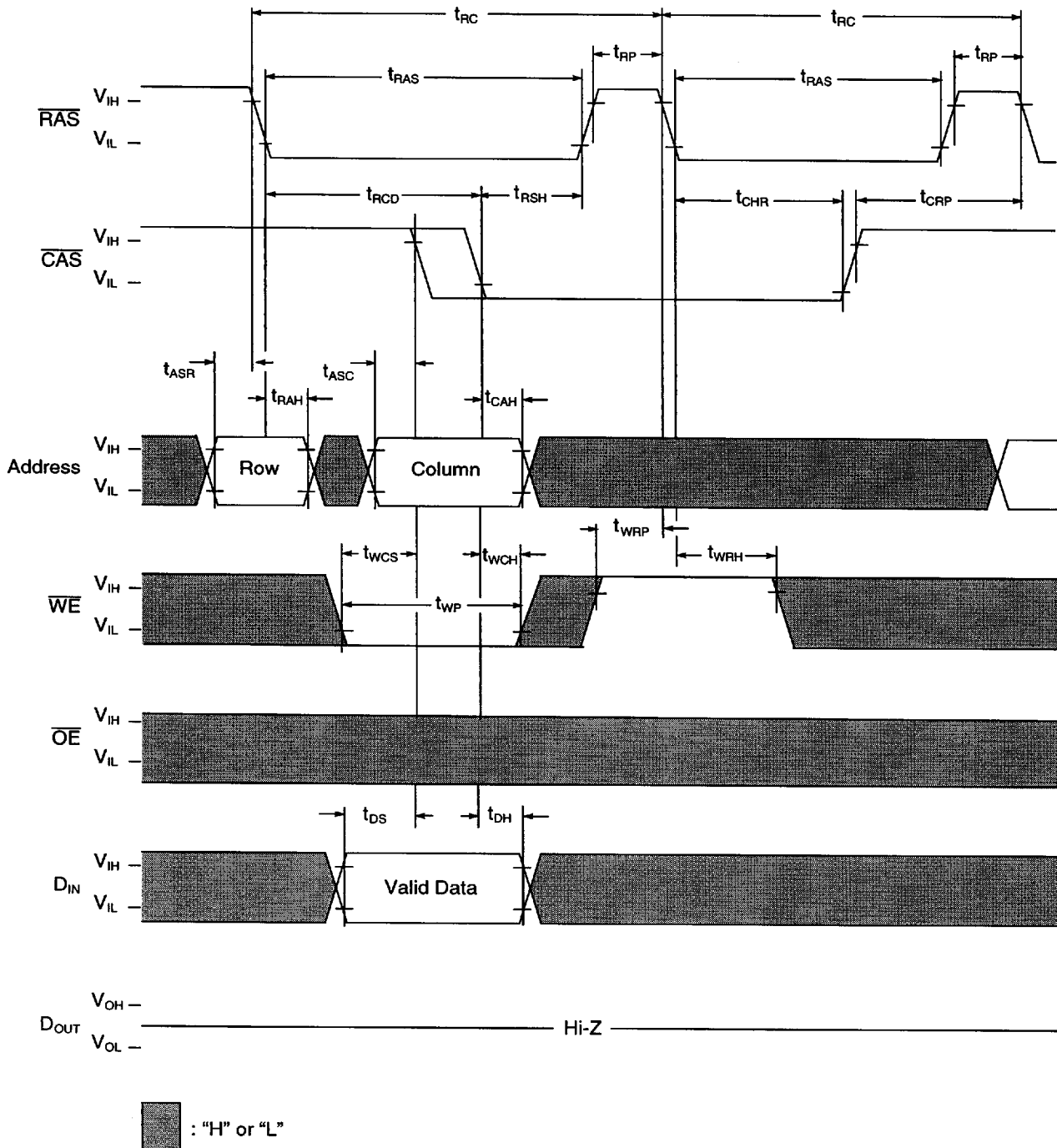


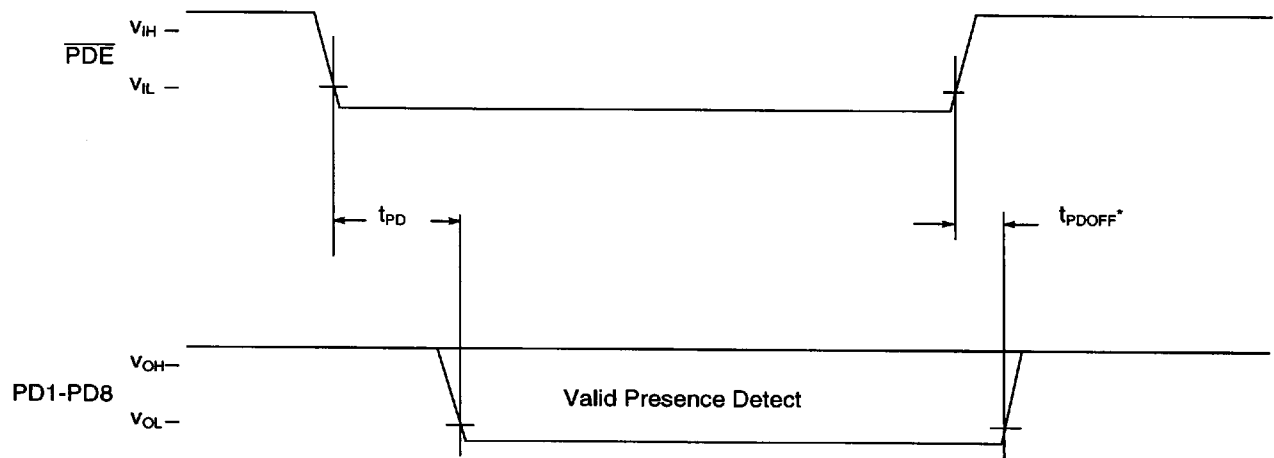
NOTE: Address is "H" or "L"

Hidden Refresh Cycle (Read)



Hidden Refresh Cycle (Write)

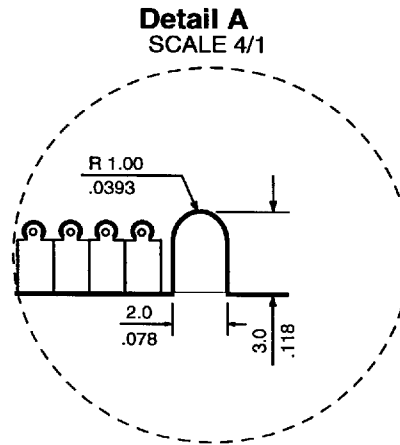
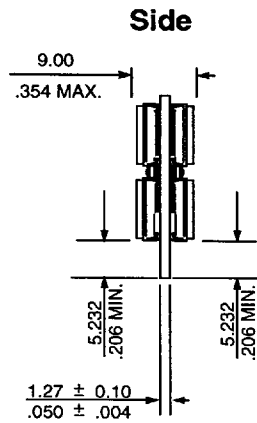
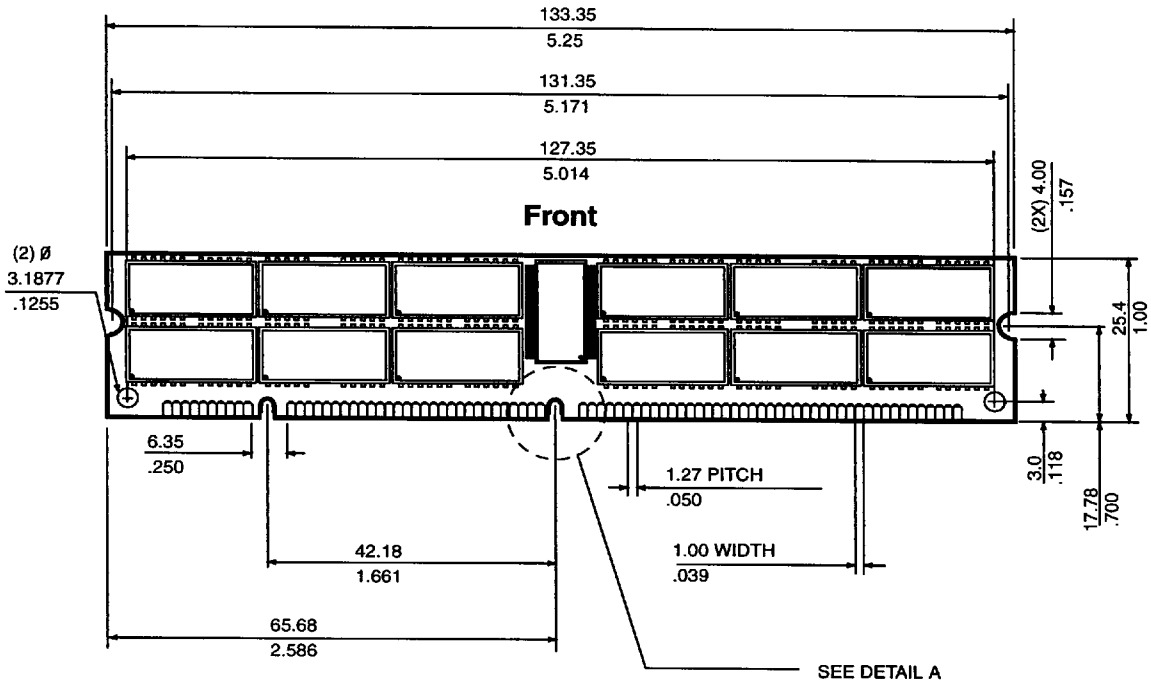


Presence Detect Read Cycle

*PD pins must be pulled high at next level of assembly

4M x 72 DRAM MODULE

Layout Drawing



Note: All dimensions are typical unless otherwise stated. Millimeters
Inches

Revision Log

Rev	Contents of Modification
08/93	Initial release of 4Mx64 and 4Mx72 DIMM specs using x1 and x4 DRAMs.
7/94	Split x72 and x64 DIMM specifications. - Significant text modifications to all areas of specification - Capacitance values modified - Read-Modify-Write and Late Write timings removed (due to use of 4Mx1 devices for parity)
7/95	Updated Ordering Information Added Hidden Refresh Deleted any references to RMW and Late Write Added Overshoot/Undershoot information Added PD/ID capacitance; added \overline{PDE} note 3 to PD table Updated Layout Drawing
5/96	Updated ordering information Added timing: t_{CAS} Improved timings: t_{CAH} , t_{CRP} , t_{DH} , t_{RRH} , t_{OEZ} , t_{CDD} , t_{OFF} , t_{CSR} , t_{CHR}